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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

**Complete if Known**

<b>Application Number</b>	09/535,015
<b>Filing Date</b>	March 24, 2000
<b>First Named Inventor</b>	Shunpei YAMAZAKI et al.
<b>Group Art Unit</b>	2811
<b>Examiner Name</b>	S. Crane
<b>Attorney Docket Number</b>	0756-2131

Sheet	1	of	1
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## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
SC		NEMANICH, R.J. et al., <i>Structure and Growth of the Interface of Pd on a-SiH</i> , The America Physical Society - Physical Review, Vol. 23, No. 12, Pages 6828-6831, June 1981.	

**Examiner  
Signature**

/Sara Crane/

Date  
Considered

05/12/2006

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Sheet	1	of	1	Attorney Docket Number	0756-2131

[illegible][illegible]

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		<del>NEMANICH, R.J. et al., Structure and Growth of the Interface of Pd on a-SiH<sub>4</sub>, The America Physical Society - Physical Review, Vol. 23, No. 12, Pages 6628-6231, June 1981. see I.D.S. of May. 02 2006</del>	

Examiner Signature	/Sara Crane/	Date Considered	05/12/2006
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Form FDO-1449  
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Patent and Trademark Office

Attorney Docket No. 0756-2131

Serial No. Not Yet Assigned

**INFORMATION DISCLOSURE STATEMENT**

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI et al.

Filing Date: March 24, 2000

Group: 2811

jc598 U.S. PTO  
09/539015  
03/24/00**U.S. PATENT DOCUMENTS**

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
SWL	5,403,772	04/04/95	Zhang et al			
	5,426,064	06/20/95	Zhang et al			
	5,481,121	01/02/96	Zhang et al			
	5,488,000	01/30/96	Zhang et al			
	5,492,843	02/20/96	Adachi et al			
	5,501,989	03/26/96	Takayama et al			
	5,508,533	04/16/96	Takemura			
	5,529,937	06/25/96	Zhang et al			
	5,534,716	07/09/96	Takemura			
	5,543,352	08/06/96	Ohtani et al			
	5,563,426	10/08/96	Zhang et al			
	5,569,610	10/29/96	Zhang et al			
	5,569,936	10/29/96	Zhang et al			
	5,580,792	12/03/96	Zhang et al			
	5,585,291	12/17/96	Ohtani et al			
SWL	5,589,694	12/31/96	Takayama et al			

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

5/11/2000 SWL	<del>R.J. Nemanich et al, "Structure and Growth of the Interface of Pd on <math>\alpha</math>-SiH", The American Physical Society - Physical Review, Vol. 22, No. 12, pp. 6828-6831, June 1981</del>
SWL	M.J. Thompson et al, "Silicide Formation in Pd- $\alpha$ -Si:H Schottky Barriers", Appl. Phys. Lett., Vol. 39, No. 3, pp. 274-276, August 1981
SWL	Hayashi et al., "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method", IEEE IEDM 1995, pages 829-832.
SWL	R.J. Nemanich et al, "Initial Phase Formation at the Interface of Ni, Pd, or Pt and Si", Mat. Res. Soc. Symp. Proc., Vol. 25, 1984

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